

# Fast switching diode chip in EMCON 3-Technology

## **FEATURES:**

- 600V EMCON 3 technology 70 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

## This chip is used for:

power module



## Applications:

• drives

Chip Type	$V_R$	I <sub>F</sub>	Die Size	Package
SIDC26D60C6	600V	100A	6.53 x 4.02 mm <sup>2</sup>	sawn on foil

#### **MECHANICAL PARAMETER:**

Raster size	6.53 x 4.02			
Area total / active	26.25 / 22.23	mm <sup>2</sup>		
Anode pad size	5.83 x 3.32			
Thickness	70	μm		
Wafer size	150	mm		
Flat position	180	deg		
Max. possible chips per wafer	554 pcs			
Passivation frontside	Photoimide			
Anode metallization	3200 nm AlSiCu			
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding			
Die bond	electrically conductive glue or solder			
Wire bond	AI, ≤500μm			
Reject ink dot size	Ø 0.65mm; max 1.2mm			
Recommended storage environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C			

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# **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	V
Continuous forward current limited by	1_		1)	- A
$T_{jmax}$	I <sub>F</sub>			
Maximum repetitive forward current	1		200	
limited by T <sub>jmax</sub>	<b>/</b> FRM		200	
Operating junction and storage temperature	$T_{\rm j}$ , $T_{ m stg}$		-40+175	°C

<sup>1)</sup> depending on thermal properties of assembly

# Static Electrical Characteristics (tested on chip), $T_i$ =25 °C, unless otherwise specified

Parameter	Symbol	Cond	Value			Unit	
raiailletei	Syllibol	Cona	itions	min.	Тур.	max.	Oiiit
Reverse leakage current	$I_{R}$	V <sub>R</sub> =600V	<i>T<sub>j</sub></i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V <sub>Br</sub>	I <sub>R</sub> =0.25mA	<i>T<sub>j</sub></i> =25°C	600			V
Forward voltage drop	$V_{F}$	$I_F = 100A$	<i>T<sub>j</sub></i> =25 °C	1.2	1.6	1.9	V

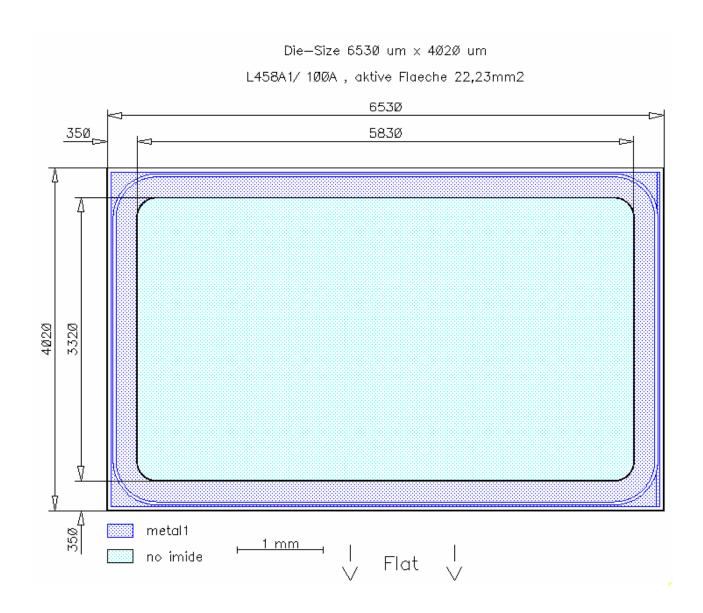
# Dynamic Electrical Characteristics (verified by design/characterization), inductive load

Parameter	Symbol	Conditions		Value 2)			Unit
raiailletei	Syllibol			min.	Тур.	max.	Julit
Peak reverse recovery current	I <sub>RM</sub>	$I_F$ =100A di/dt=5100A/ms $V_R$ =300V $V_{GE}$ = -15V	$T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$ $T_j = 150 \text{ °C}$		130 150 160		A
Recovered charge	Q <sub>r</sub>	$I_F$ =100A di/dt=5100A/ms $V_R$ =300V $V_{GE}$ = -15V	$T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$ $T_j = 150 \text{ °C}$		4.00 8.00 10.0		μC
Reverse recovery energy	E <sub>rec</sub>	$I_F$ =100A di/dt=5100A/ms $V_R$ =300V $V_{GE}$ = -15V	$T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$ $T_j = 150 \text{ °C}$		1.30 2.25 2.75		mJ

<sup>&</sup>lt;sup>2)</sup> values also influenced by parasitic L- and C- in measurement and package.



## **CHIP DRAWING:**





# FURTHER ELECTRICAL CHARACTERISTICS: This chip data sheet refers to the device data sheet PS100R06KE3 Description: AQL 0,65 for visual inspection according to failure catalog Electrostatic Discharge Sensitive Device according to MIL-STD 883 Test-Normen Villach/Prüffeld

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